Quality System for producing discrete semiconductor devices and integrated circuits conforms to the requirements of STB ISO 9002-96

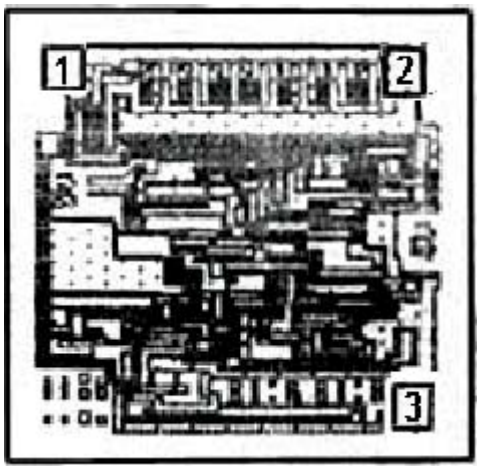
78L06AC — CHIP FOR THREE-TERMINAL POSITIVE VOLTAGE REGULATOR IC

Features:

- ✧ Output current in excess of 100 mA
- ✧ No external components required
- ✧ Internal short circuit current limiting
- ✧ Internal thermal overload protection
- ✧ Available in either ± 5% selections

Physical Characteristics:

Wafer Diameter ……100 ± 0.5 mm
Wafer thickness ….. 420 ± 20 μm;
Die size …….. 1.3 x 1.2 mm^2 ;
Scribe width ……... 80 μm
Passivation ……. PSG



Pad #	Pad name	Description	Bond Pad (μm)
1	OUT	Output	101 x 101
2	IN	Input	101 x 101
3	GND	Ground	101 x 101

Substrate is Common and should be connected to Pad 2

- ♦ Maximum Ratings (Ta = 25°C)
- ♦ Input Voltage – 30V
- ♦ Operating Junction Temperature (Tj = 125°C)

ELECTRICAL CHARACTERISTICS CHIPS ON WAFER (Ta=25°C)

(Vin= 11 V, Io=40mA, Ci=0.33μF, Co=0.1μF, Tj = + 25°C, unless otherwise noted.)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Output Voltage	Vo	8V ≤ Vin ≤ 21V,1mA ≤ Io ≤ 40mA 1mA ≤ Io ≤ 70mA	5.77 5.77	6.23 6.23	V
Line Regulation	ΔVv	8 V ≤ Vin ≤ 21 V 9 V ≤ Vin ≤ 21 V		144 99	mV
Load Regulation	ΔVi	1mA ≤ Io ≤ 100mA 1mA ≤ Io ≤ 40mA		63 32	mV
Quiescent Current	Ib			5.8	mA
Quiescent Current Change	ΔIb	9 V ≤ Vin ≤ 21 V 1mA ≤ Io ≤ 40mA		1.4 0.09	mA

* The parameters are guaranteed after scribing and chip encasement.

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